

### preliminary

$V_{\text{RRM}}$	=	45 V
I <sub>FAV</sub>	=	300 A
V <sub>F</sub>	=	0.76 V

High Performance Schottky Diode Low Loss and Soft Recovery Single Diode

Schottky Diode Gen<sup>2</sup>

Part number

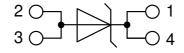
**DSA300I45NA** 



Backside: Isolated



20200127b



### Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

### **Applications:**

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

### Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper
- internally DCB isolated
- Advanced power cycling

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IXYS reserves the right to change limits, conditions and dimensions.



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Schottky					Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RSM</sub>	max. non-repetitive reverse block	ing voltage	$T_{VJ} = 25^{\circ}C$			45	V
V <sub>RRM</sub>	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			45	V
I <sub>R</sub>	reverse current, drain current	$V_{R} = 45 V$	$T_{VJ} = 25^{\circ}C$			3	mA
		$V_R = 45 V$	$T_{vJ} = 150^{\circ}C$			30	mA
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 300 A	$T_{vJ} = 25^{\circ}C$			0.84	V
		$I_{F} = 600 \text{ A}$				1.14	V
		I <sub>F</sub> = 300 A	T <sub>vJ</sub> = 125°C			0.76	V
		$I_{F} = 600 \text{ A}$				1.10	V
I FAV	average forward current	T <sub>c</sub> = 100°C	T <sub>vJ</sub> = 150°C			300	Α
		rectangular d = 0.5					
V <sub>F0</sub>	threshold voltage		T <sub>vJ</sub> = 150°C			0.41	V
r <sub>F</sub>	slope resistance } for power lo	oss calculation only				1.12	mΩ
$\mathbf{R}_{thJC}$	thermal resistance junction to cas	е				0.15	K/W
R <sub>thCH</sub>	thermal resistance case to heatsing	nk			0.1		K/W
P <sub>tot</sub>	total power dissipation		$T_c = 25^{\circ}C$			830	W
I <sub>FSM</sub>	max. forward surge current	t = 10 ms; (50 Hz), sine; $V_{R} = 0 V$	$T_{VJ} = 45^{\circ}C$			4.80	kA
C	junction capacitance	$V_{\rm R} = 5V$ f = 1 MHz	$T_{vJ} = 25^{\circ}C$		16.5		nF

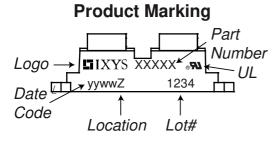
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Package	Package SOT-227B (minibloc)				Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per terminal 1)					150	А
$\mathbf{T}_{v_J}$	virtual junction temperature	)			-40		150	°C
T <sub>op</sub>	operation temperature				-40		125	°C
T <sub>stg</sub>	storage temperature				-40		150	°C
Weight						30		g
M <sub>D</sub>	mounting torque				1.1		1.5	Nm
M <sub>T</sub>	terminal torque				1.1		1.5	Nm
d <sub>Spp/App</sub>	araanaa diatanaa an aurfa	ce   striking distance through air	terminal to terminal	10.5	3.2			mm
d <sub>Spb/Apb</sub>	creepage distance on suna	ice   suiking distance unough an	terminal to backside	8.6	6.8			mm
V	isolation voltage	t = 1 second			3000			V
		t = 1 minute	50/60 Hz, RMS; liso∟ ≤ 1 mA		2500			V

<sup>1)</sup> I<sub>must</sub> is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.



### Part description

- D = Diode S = Schottky Diode
- A = low VF 300 = Current Rating [A]
- I = Single Diode
- 45 = Reverse Voltage [V]
- NA = SOT-227B (minibloc)

Order	ring	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Stand	ard	DSA300I45NA	DSA300I45NA	Tube	10	511251

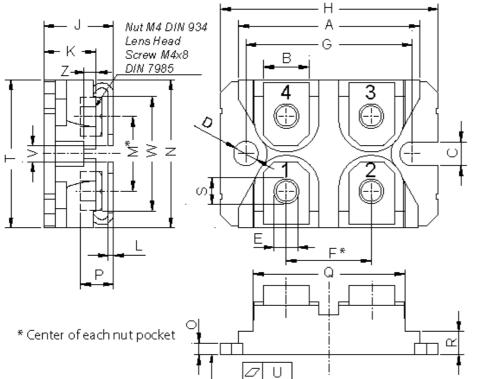
Similar Part	Package	Voltage class
DSA300I100NA	SOT-227B (minibloc)	100
DSA300I200NA	SOT-227B (minibloc)	200

Equiva	alent Circuits for	Simulation	* on die level	$T_{VJ} = 150^{\circ}C$
	)[R	Schottky		
V <sub>0 max</sub>	threshold voltage	0.41		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	0.28		mΩ

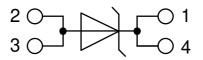


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## Outlines SOT-227B (minibloc)



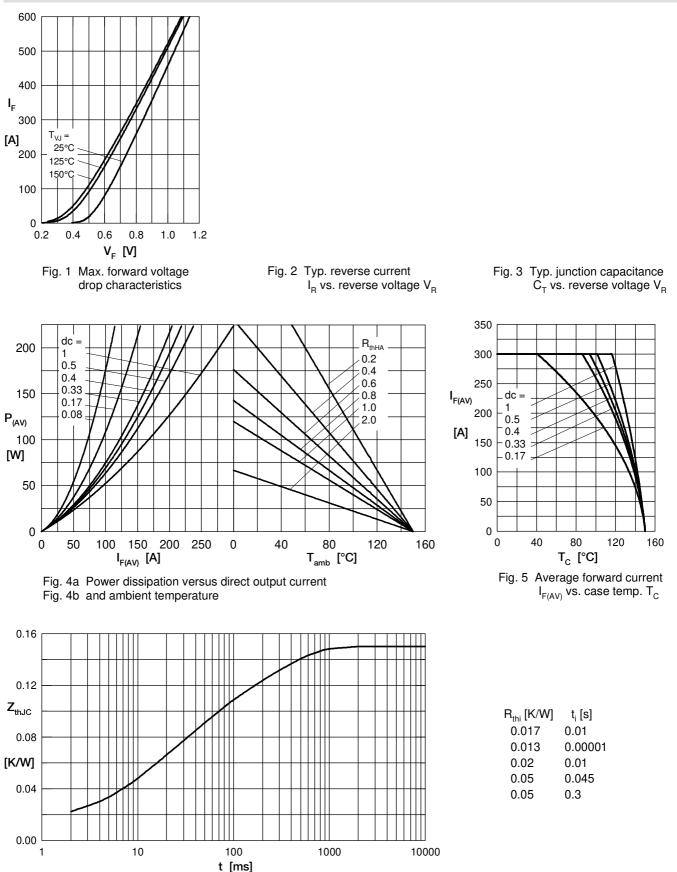
Dim.	Millir	neter	Inc	hes
Dim.	min	max	min	max
Α	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
С	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
Н	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
К	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
Μ	12.50	13.10	0.492	0.516
Ν	25.15	25.42	0.990	1.001
0	1.95	2.13	0.077	0.084
Ρ	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
Т	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Ζ	2.50	2.70	0.098	0.106

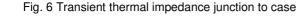




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